

ABSTRACT

A method of processing a surface of a nitride semiconductor crystal, wherein a surface of a nitride semiconductor crystal (11) is brought into contact with a liquid containing at least Na, Li or Ca as a processing solution (15). In the method, the 5 processing solution (15) can be a liquid containing at least Na, having an Na content of 5-95 mol%. The processing solution (15) can be a liquid containing at least Li, having an Li content of 5-100 mol%. A nitride semiconductor crystal having a maximum depth of a surface scratch of at most 0.01 μm or an average thickness of a damaged layer of at most 2 μm . Consequently, a method of processing a surface of a nitride 10 semiconductor crystal with a decreased depth of a surface scratch or a decreased thickness of a damaged layer, and a nitride semiconductor crystal obtained with the method can be provided.

USPS EXPRESS MAIL
EV 511 024 341 US
MAY 18 2005